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(54) Laser-based system for the total repair of photomasks.

(57) A low power laser-based system for repairing clear and opaque defects in a photomask. The system includes a laser source for providing a beam having a wavelength between 0.40  $\mu\text{m}$  and 2.0  $\mu\text{m}$ . The beam is coupled to a computer controlled scanning device which scans the beam across a defective area of the photomask to repair the defect by thermal deposition of micron-size films on the defect or by laser-induced degradation of a polymer coating the defect. Excess metal is removed from the photomask surface via laser vaporization.

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## TECHNICAL FIELD

The present invention relates to a system for repairing both clear and opaque defects in photomasks.

## BACKGROUND OF THE INVENTION

05           The process of fabricating photomasks (usually chrome or iron oxide on soda, lime, glass or quartz) typically leaves behind several defects. The defects can be classified as opaque or clear; the former relating to the case where excess chrome exists  
10 in an unwanted area, the latter relating to the case where chrome is missing from a desired area. These defects can also arise during use of the mask in standard lithographic processes.

          Currently, it is possible to repair opaque  
15 defects (i.e., remove excess chrome) by laser vaporization. The repair of clear defects is much more complex.

          The conventional method of repairing clear defects relies on a lift-off process, i.e. spinning on  
20 photoresist, sputtering on a metal, followed by liftoff. This process is not only time consuming and expensive, but also runs the risk of introducing new defects since the entire photomask is affected. In addition, high resolution, e.g. the repair of a 2 $\mu$ m  
25 diameter pinhole, may be difficult to achieve.

          Another more site-specific method exists. Here, a microdrop of ink is dispensed on the clear

defect, and then the entire photomask is baked in an oven to promote adhesion. This process is of limited resolution. Defects less than  $10\mu\text{m}$  square usually cannot be repaired. Furthermore, the repair is not durable--it is easily removed during standard photomask cleaning procedures.

Another site-specific method for defect repair employs an ultraviolet laser (typically at  $257\text{nm}$ ). Here, the laser is used in conjunction with a metal-bearing gas. The laser light photo-dissociates (i.e., breaks the molecular bonds) the molecules in the vapor phase. The metal fragments subsequently impinge on the surface eventually forming a thin film.

This procedure is difficult to employ in the semiconductor industry. Ultraviolet lasers generally occupy an inordinate amount of space. Since clean room space, where the repair takes place, is limited and costly, such a repair system is undesirable. In addition, ultraviolet laser light particularly that generated at  $257\text{ nm}$ , is unstable and unreliable, thus making such a system undesirable in a production environment. The required ultraviolet optics is also difficult to obtain and costly.

In terms of laser-based systems for opaque defect repair, several problems are also encountered. For example, such systems depend on mechanical scanning stages for the positioning of the defect area under the laser irradiation zone. To avoid the large costs involved, manufacturers typically employ low-resolution stages--typically  $10\mu\text{m}$  for positioning. Finer adjustments must be made manually. This slows down the repair process and makes the accurate repair of small defects on the order of  $1\mu\text{m}$  very difficult.

Further, such systems do not have the capability of scanning over small areas say 10 m square. Thus, to remove excess chrome in such an area would require several individual laser repairs, i.e.

05 the area in which chrome is to be removed would have to be brought under the laser irradiation zone in several discrete steps.

#### SUMMARY OF THE INVENTION

In accordance with the present invention, the

10 disadvantages of prior photomask repair systems have been overcome. The system of the present invention is a low-power laser based system for repairing both clear and opaque defects in a photomask.

The system of the present invention includes

15 a laser source for providing a beam having a wavelength between 0.40 $\mu$ m and 2.0 $\mu$ m, the power level of the laser source being less than or equal to 2 watts. The laser source is capable of continuous operation during the photomask repair process. An acousto-optical scanning

20 device is provided to position and/or scan the laser beam across a predetermined area of the photomask so that small defects may be accurately repaired. Imaging/focusing optics are coupled to the output of the scanning/positioning device to allow simultaneous

25 viewing of the photomask and focusing of the laser beam on a predetermined area of the photomask. In addition, the system includes an acousto-optic modulator interfaced to a computer for the automatic control of

the intensity and pulse duration of the laser beam in response to the power of the laser transmitted through the repair area as sensed by a detector. The computer is compatible with photomask inspection systems such as those manufactured by a commercially available photomask inspection system. Thus, information regarding the location of a photomask defect can be fed in from the commercially available photomask inspection system into the computer. The computer then drives a low resolution X-Y stage which will bring the defect into the optical field of view. The computer is then used to control the scanning/positioning device to accurately position the laser beam with respect to the defect on the photomask and/or to scan a pre-determined area on the photomask. The computer-controlled positioning of the laser beam with respect to the defect is aided by a numbered grid which is superimposed on the monitor's image of the photomask.

The system may be employed to repair clear defects on a photomask by a method utilizing laser-induced degradation of a novolak-based polymer coating the photomask. In carrying out this method, the scanning device of the system scans the laser beam across the defective area of the photomask for localized heating thereof to darken the polymer coating the photomask. The surface power of the laser as sensed by the detector provides an indication of the darkening level of the polymer and in response thereto, the computer controls the power level of the laser beam to heat the polymer coating the photomask to a temperature between 200°C and 500°C so as to brown the polymer. When the detector indicates that the polymer

has been adequately browned, the computer, in response thereto increases the power level of the laser beam to heat the polymer to a temperature which is greater than 500°C so as to char the polymer.

05           The system may also be employed to repair clear defects on a photomask by thermal deposition of micron-size metallic films. In order to carry out this method, a photomask is positioned in a gas cell containing a metal-bearing gaseous compound. A  
10 nucleation layer is formed on a surface of the photomask by shining ultraviolet light thereon. After the nucleation layer is formed, the system of the present invention is employed to focus the lower power laser beam on a defective surface of the photomask for  
15 localized heating of the area of the photomask to which the beam is incident to thermally decompose molecules of the metal-bearing gaseous compound on the heated area to deposit a metal film thereon.

          These and other objects and advantages of the  
20 invention, as well as the details of an illustrated embodiment, will be more fully understood from the following description and the drawings.

#### BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a block diagram of the photomask  
25 repair system of the present invention;

FIG. 2 is a cross-sectional view of a gas cell which may be used with the system of FIG. 1; and

FIG. 3 is a representation of the path that the laser follows when scanning a clear or opaque defect.

#### DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENT

05           The system of the present invention repairs clear and opaque defects in a photomask 10 which is securely attached to a low-resolution X, Y scanning table 12. The table 12 also contains a low-resolution Z travel. The system employs a laser source 14, the  
10 power level of which is less than or equal to 2 watts, the beam having a wavelength between 0.40 $\mu$ m and 2.0 $\mu$ m. The laser source 14 may be a gas laser such as a HeNe or argon ion laser. A solid state laser source such as a GaAs or a GaAlAs laser can also be used having the  
15 property of being extremely compact.

          The laser beam from the source 14 is directed into a modulator/attenuator 16. The modulator may be an acousto-optical modulator which is used to adjust the pulse duration of the laser beam in response to a  
20 control signal from a computer 18. The modulator is also used as a shutter capable of providing a single laser pulse of a predetermined duration. In the preferred embodiment, the shutter speed is adjusted between 0.4 $\mu$ s and 2.0 $\mu$ s. The attenuator adjusts the  
25 power level or intensity of the laser beam. The power level of the laser beam at the surface of the photomask can also be controlled by the attenuator, the attenuator varying the surface laser power between 0.01

milliwatts and 100 milliwatts. The modulator/attenuator 16 may be such as manufactured by Newport Electro-Optics and Intra Action, although other types of modulator/attenuators such as electro-optical  
05 may be suitable for use in the system of the present invention.

The beam output from the modulator/attenuator 16 is coupled to an X, Y scanning/positioning device 20 which may be an acousto-optical, electro-optical or  
10 mechanical scanning device capable of scanning and/or positioning the laser beam across a very small area such as a  $128\mu\text{m} \times 128\mu\text{m}$  area continuously or positioning the beam anywhere within this area. A suitable scanning/positioning device is also  
15 manufactured by Newport Electro-Optics and Intra Action. The laser beam output from the scanning device 20 is reflected into a high power focusing objective 52 via reflector 55. The objective focuses the beam to its diffraction-limited spot size. In the preferred  
20 embodiment, the objective has a numerical aperture of 0.2 or higher and a magnification of 20x or higher. The objective also facilitates the simultaneous viewing of the photomask by the operator. The photomask may be illuminated either by a set of reflected-light optics  
25 44 or transmitted-light optics 46 which is directed through the photomask and objective via reflector 54. The sample and laser beam are simultaneously brought into focus by adjusting the Z (i.e., distance between photomask and objective) position of the mechanical  
30 stage 12. In addition, fine focusing is accomplished by the computer control of the piezoelectric driver 50 onto which the objective 52 is mounted. Sample viewing



and laser beam positioning is facilitated by directing the light from the photomask via reflector 58 into video camera 22. The image of the photomask is then formed on monitor 24. The monitor 24 also has a  
05 numbered grid superimposed on it. This grid corresponds to an area of  $128\mu\text{m} \times 128\mu\text{m}$  on the photomask. Depending on the particular computer system used, a variety of grid sizes may be used. The grid size is chosen to be compatible with the bit-size of  
10 the computer.

The table 12 on which the photomask 10 is positioned may be transparent or may include an aperture 26 which allows the laser beam, transmitted through the photomask, to pass to a detector 28. The  
15 detector 28 is responsive to the beam transmitted thereto for sensing the amount of power at the surface of the photomask 10. The detector 28 provides a signal representing the surface laser power to the computer control 18 which in response thereto provides a control  
20 signal to the modulator/attenuator 16 to vary the intensity of the laser beam as described below.

The computer control 18 also controls the positioning of the laser beam with respect to the photomask 10. The computer control 18 may be  
25 compatible with the commercially available photomask inspection system which stores the location of the photomask defects. This data can then be used by computer 18 to control the mechanical movement of the table 12 in the X and Y directions in order to locate  
30 the defect approximately under the beam. Thus, data obtained independently by a photomask inspection system can be used to control the table 12. The mechanical

movement of table 12 provides coarse positioning of the photomask with respect to the laser beam. The computer control 18 also controls the scanning/positioning device 20 to precisely locate the beam with respect to the photomask. The determination of the precise location on the photomask is aided by the numeric grid superimposed on the television monitor 24. The coordinates of the defect as obtained from the grid on the monitor 24 are then fed into the computer 18 which in turn controls the scanning/positioning device 20 which precisely locates the focused laser beam onto the defect area. The scanning device 20 under the control of the computer 18 thus provides fine adjustments in the positioning of the beam with respect to the photomask 10.

The system shown in FIG. 1 may be employed to carry out a method wherein clear defects on the photomask 10 are repaired by laser-induced degradation of a polymer coating the photomask. In order to carry out this method, the surface 30 of the photomask is coated with a novolak-based polymer, preferably a positive photoresist, to provide a coating layer having a thickness between 2,000A and 20,000A.

Other polymers may be used provided that they char or darken in response to heating; the polymer must also adhere satisfactorily when coated on the photomask. In addition, the polymer coating must be pinhole free. Furthermore, the uncharred region of the polymer must be capable of being removed easily without damaging the photomask. Another requirement of the particular polymer used by the subject method is that the charred region must have an optical density of at

least 2.5 and be able to withstand the rigorous cleaning method normally encountered in photomask cleaning.

05 The coating procedures used are standard procedures and are well-known to those skilled in the art. Very basically, the polymer is sprayed on the photomask as the photomask is spun so that a relatively uniform coating results across the surface of the photomask. After coating the photomask 10 with the polymer, the photomask is positioned on the table 12, and the laser beam is scanned by the device 20 across the defective area of the photomask to heat the polymer coating to a temperature between 200°C and 500°C so as to brown the polymer. The detector 28 senses the power of the laser at the surface of the photomask to provide a signal representative thereof and of the power absorption of the photomask to provide an indication of the darkening level of the polymer. The computer 18 in response to the signal output from the detector 28 determines when the polymer coating has been adequately browned by the laser beam and in response to such a determination varies the control signal applied to the modulator/attenuator 16 to increase the intensity of the laser beam so as to heat the polymer to a temperature which is greater than 500°C to further darken or char the polymer.

After the polymer is charred, that portion of the polymer which is not exposed to the laser is removed by immersing the photomask 10 in an organic solvent such as a keytone alcohol or inorganic solvent such as an alkali, and in the preferred embodiment, acetone is used as the solvent. The charred portion of

the polymer has undergone a significant change in chemistry so that it is relatively insoluble with respect to the uncharred portion of the polymer. Although the mechanism by which the charred portion of the polymer becomes relatively insoluble is not completely understood, it is believed that the charred polymer has a much higher carbon ratio which, in turn, reduces its solubility. Further details of the method for providing laser-induced polymer degradation for photomask repair may be found in our co-pending application (claiming priority of U.S. patent application Serial Number 622367), entitled "Method for repairing a Photomask by laser-induced polymer degradation" filed concurrently herewith, which is incorporated herein by reference.

The system shown in Figure 1 may also be employed to carry out a method of repairing clear defects in a photomask by thermal deposition of micron-size metallic films on the photomask. In order to carry out this method, the photomask 10 is positioned in a gas cell 32 which contains a metal-bearing gaseous compound 34. The gas cell 32 includes metal end plates 36 and 38 and a transparent window 40. The window 40 may, for example, be made of quartz. The photomask 10 may also form a window of the gas cell 32 with the surface 42 on which a metal deposit is to be made forming an inner surface of the cell.

After positioning the photomask 10 in the gas cell 32, a nucleation layer is formed on the photomask to seed the surface 42 thereof. The nucleation layer is a random deposit of parts of the gaseous compound 34 on the surface 42 of the photomask forming one or a few monolayers on the substrate surface which are

substantially invisible and removable. The nucleation layer may be formed on the photomask 10 by shining ultraviolet light through the window 40 onto the surface 42 of the photomask 10 to randomly deposit parts of the metal-bearing compound 34 on the photomask.

After the nucleation layer is formed, the gas cell 32 is positioned on the table 12. The laser beam is then focused onto the defective surface on the photomask for localized heating of an area of the photomask to which the laser beam is incident to thermally decompose molecules of the gaseous compound 34 on the heated area to deposit a metal film thereon. Metal films are thermally deposited on the desired areas of the photomask by scanning the beam across these areas under the control of the scanning device 20. Details of the method for thermal deposition of micron-size metallic films on a photomask may be found in our co-pending application (claiming priority of U.S. patent application Serial Number 822366), entitled "Method for Depositing a Micron-Size Metallic Film on a Transparent Substrate Utilizing a Visible Laser", filed concurrently herewith, which is incorporated herein by reference.

The system of Figure 1 may also be employed to remove opaque defects from the photomask 10. In order to remove opaque defects (i.e. excess chrome), the computer 18 controls the modulator/attenuator 16 to adjust the power of the laser beam to a level which will remove the metal patterns from the surface of the photomask 10 as well known in the art. The scanning/positioning device 20 then scans the beam across the defective area of the photomask to remove \_\_\_\_\_

any unwanted metal deposits. The scanning/positioning device 20 can also be used to select a single  $1\mu\text{m}$  area of the photomask for removal of chrome. The system of FIG. 1 represents an improvement over prior-art opaque-defect repair systems for the following reasons.

05 First, the system described herein causes the laser to be scanned in response to commands by computer across the opaque defect in a continuous-path rather than normally moved across the defect in discreet steps.

10 Second, in prior art systems, the photomask is moved in discreet steps with respect to the laser rather than moving the laser in a continuous path with respect to the photomask as taught by the subject invention. By scanning the laser with respect to the photomask, the

15 speed of the process can be greatly increased and the system taught by the present invention the opaque defect area is divided into rectangular sections, and the coordinates of each corner of each rectangle is determined from the grid on the monitor and then fed

20 into the computer. The computer then causes the laser to be automatically scanned in a boustrophedonic path until the entire area of the rectangle has been covered. This removes all of the metal within that rectangle. The same process is then repeated for each

25 rectangular area until the entire opaque defect is repaired. The path that the laser follows is illustrated in FIG. 3.

The scanning process used by the laser is similar when the laser is used to repair clear defects.

30 Both opaque and clear defects can be repaired in one processing sequence. This can be accomplished in one of two ways. One way to accomplish both clear and

opaque defect repair in a single process is to coat the photomask with the novolak-based polymer. Next, darken the polymer over the clear defects. Then, ablate the polymer over the opaque defects, followed by vaporizing the metalization forming the opaque defect. Another way to repair both clear and opaque defects in a single process is to place the photomask in a cell containing a metal-bearing gaseous compound. Next, the laser beam is focused on the clear defect to deposit metal over the clear defect area. Then, the cell is vented to removed the metal-bearing gaseous compound. The laser is then focused on the opaque defect to vaporize the metal forming the opaque defect.

Although the invention has been described and illustrated in detail, it is to be clearly understood that the same is by way of illustration and example only, and is not to be taken by way of limitation; the spirit and scope of this invention being limited only by the terms of the appended claims.

WE CLAIM:

1. An instrument for repairing both clear and opaque micron-size defects in photomasks comprising:
  - 05 a laser source providing a beam having a wavelength between 0.40 $\mu$ m and 2.0 $\mu$ m;
  - optical means for viewing the photomask within an optical field of view;
  - means for locating defective areas on the photomask within the optical field of view;
  - 10 means for focusing the laser on the photomask;
  - means for precisely positioning the focused laser beam at a predetermined area on the photomask;
  - means for continuously scanning the focused laser beam over a predetermined area;
  - 15 means for adjusting the laser power; and
  - means for selecting the number of laser pulses and their duration.
2. An instrument as recited in Claim 1 wherein said laser source is a solid state laser.
3. An instrument as recited in Claim 1 wherein said laser source is a gas laser.
4. An instrument as recited in Claim 1 wherein said optical means includes:
  - a high-power focusing objective for creating an image of the photomask;



05           a camera for receiving the image from the  
            objective; and  
            a monitor to display the image from the  
camera.

5. An instrument as recited in Claim 4  
wherein said monitor provides a visual display of the  
defective areas of the photomask and the focused laser  
beam.

05           6. An instrument as recited in Claim 4  
wherein said monitor includes a screen and further  
includes a numbered grid superimposed on the monitor  
screen to provide a means for assigning an absolute  
coordinate of any area of the photomask within the  
objective's field of view.

7. An instrument as recited in Claim 6  
wherein said numbered grid is 128 x 128.

8. An instrument as recited in Claim 6  
wherein said numbered grid is 512 x 512 or less.

9. An instrument as recited in Claim 1  
further including a set of reflected and transmitted  
light optics for the illumination of the photomask.

10. An instrument as recited in Claim 1  
further including a computer-controlled low resolution  
X, Y table for bringing the defective areas of the  
photomask into the optical field of view.

11. An instrument as recited in Claim 10 wherein said computer controls movement of said table using data obtained from an independent photomask inspection system.

12. An instrument as recited in Claim 11 wherein said data specifies the location of the defects on the photomask and is used by the computer to drive the X, Y stage.

13. An instrument as recited in Claim 1 further including a high-power objective wherein the focusing of the laser beam on the photomask is accomplished by directing the beam through a high power  
05 objective.

14. An instrument as recited in Claim 1 wherein said objective has a numerical aperature of 0.2 or higher.

15. An instrument as recited in Claim 1 wherein said objective has a magnification of 20x or higher.

16. An instrument as recited in Claim 13 further includes table adjustable in the X-Y and Z planes for facilitating focusing of the laser beam onto the photomask.

17. An instrument as recited in Claim 16 wherein the table is used to change the distance between the photomask and objective.

18. An instrument as recited in Claim 13 further including a piezoelectric driver on which the objective is mounted for the fine control of the distance between the objective and photomask.

19. An instrument as recited in Claim 18 further including a computer for controlling the piezoelectric driver.

20. An instrument as recited in Claim 1 further including a computer-controlled scanning/positioning device for positioning the laser.

21. An instrument as recited in Claim 20 wherein said scanning/positioning device is an acousto-optic device.

22. An instrument as recited in Claim 20 wherein said laser scanning device is an electro-optic device.

23. An instrument as recited in Claim 20 wherein said laser scanning device is a mechanical device.

24. An instrument as recited in Claim 20 further including a television monitor for determining the coordinates of the defect to produce data to be fed into the computer to control the scanning/positioning device direct the focused laser beam on to the defect.

25. An instrument as recited in Claim 1 wherein said means for continuously scanning the laser beam includes a computer controlled laser scanning device.

26. An instrument as recited in Claim 20 wherein said laser scanning device is acousto-optic.

27. An instrument as recited in Claim 20 wherein said laser scanning device is electro-optic.

28. An instrument as recited in Claim 20 wherein said scanning device moves said laser in a boustrophedonic path across the surface of the defect.

05 29. An instrument as recited in Claim 25 further including means for dividing the defect area into one or more predetermined areas and for determining the coordinates for each area, said means including a television monitor and wherein said coordinates are fed into said computer for controlling the scanning device and continuously scans the focused laser beam over the defect.

30. An instrument as recited in Claim 29 wherein the predetermined area is less than or equal to a  $128\mu\text{m} \times 128\mu\text{m}$  area.

31. An instrument as recited in Claim 29 wherein the predetermined area is less than or equal to a  $512\mu\text{m} \times 512\mu\text{m}$  area.

32. An instrument as recited in Claim 1 wherein said means for adjusting the laser power is a computer controlled modulator.

33. An instrument as recited in Claim 32 wherein said modulator is acousto-optic.

34. An instrument as recited in Claim 32 wherein said modulator is electro-optic.

35. An instrument as recited in Claim 32 wherein said computer control can adjust the laser power at the surface of the photomask between 0.01 milliwatt and 100 milliwatts.

36. An instrument as recited in Claim 1 further including a computer controlled modulator for generating laser pulses of adjustable number and duration.

37. An instrument as recited in Claim 36 wherein the modulator is acousto-optic.

38. An instrument as recited in Claim 36 wherein the laser pulse duration is selected within the range of 1μsec to 1 sec.

39. An instrument for repairing a defective area of a photomask, the photomask having a novolak-based polymer coating thereon, comprising:

05 a laser source for providing a beam having a wavelength between 0.4μm and 2.0μm;

means for scanning said beam across the defective area of the photomask for localized heating thereof to darken the polymer;

means for detecting the level of darkening of  
10 the polymer to provide a signal representative thereof;  
control means for controlling the power of said laser source; and

means responsive to said darkening level signal for controlling the power level of the laser  
15 beam to heat the polymer to a temperature between 200°C and 500°C to brown the polymer, said control means increasing the power level of the laser beam to heat the polymer to a temperature greater than 500°C to darken the polymer when the darkening level signal indicates  
20 browning of the polymer so that the optical density is at least as great as 2.5.

40. An instrument for repairing a clear defect on a photomask, the photomask being positioned in a cell containing a metal-bearing gaseous compound, comprising:

05 a laser source for providing a beam having a wavelength between 0.40μm and 2.0μm;

means coupled to said laser source for scanning and positioning said beam across a clear defect of the photomask;

10 means coupled to said laser source for positioning said beam at a clear defect of the photomask; and

means coupled to said scanning and positioning means for focusing said beam on the clear  
15 defect surface of the photomask for localized heating

of an area of the substrate to which said laser beam is incident to thermally decompose molecules of said compound on the heated area to deposit a metal film thereon.

41. An instrument for photomask repair comprising first means for repairing micron-sized clear defects; and

second means for repairing micron-sized  
05 opaque defects.

42. An instrument as recited in Claim 41 wherein said first means and said second means are accomplished using a laser.

43. An instrument as recited in Claim 42 wherein said laser provides a beam having a wave-length between 0.4 microns and 2.0 microns.

44. An instrument as recited in Claim 44 further including an optical means for viewing the photomask within an optical field of view; and  
means for locating defective areas on the  
05 photomask within the optical field of view.

45. An instrument as recited in Claim 44 including means for continuously scanning the focused laser beam of a predetermined area.

46. An instrument as recited in Claim 41 including means for continuously scanning the focused laser beam of a predetermined area.

47. An instrument as recited in Claim 42 further including means for precisely positioning a focused laser beam at a predetermined area on the photomask.

48. An instrument as recited in Claim 42 further including a means for focusing the laser on the photomask in a diffraction-limited spot size.

49. An instrument as recited in Claim 42 wherein said laser source is a solid-state laser.

50. A method for repairing clear and opaque defects on a photomask comprising:

coating said photomask with a polymer;

05 positioning said photomask with respect to a laser source such that a beam from said laser source is focused on a clear defect on said photomask;

scanning said beam across said clear defect to produce localized heating of said polymer to darken the polymer;

10 detecting the level of darkening of the polymer to provide a signal representative thereof;

means for responding to said darkening level signal for controlling the power level of the laser beam to heat the temperature between 200°C and 500°C to  
15 brown the polymer;

further increasing the power level of the laser to heat the polymer to a temperature greater than 500°C to darken the polymer when the darkening level signal indicates browning of the polymer until the



20 optical density of the polymer is at least as great as  
2.5;

repositioning the photomask with respect to  
said laser source such that a beam from said laser  
source is focused on an opaque defect on said  
25 photomask;

adjusting the power to ablate photoresist  
covering the opaque defect;

readjusting the laser power to vaporize the  
metalization forming the opaque defect.

51. An instrument for repairing a clear  
defect and an opaque defect on a photomask, the  
photomask being positioned in a cell containing a  
metal-bearing gaseous compound, comprising:

05 a laser source for providing a beam having a  
wavelength between 0.40 $\mu$ m and 2.0 $\mu$ m;

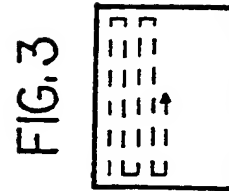
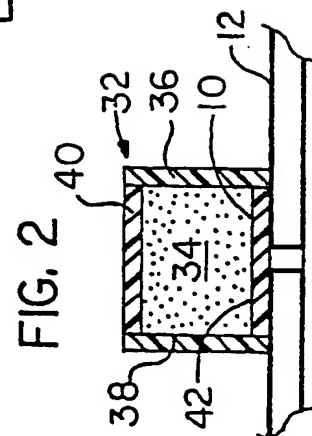
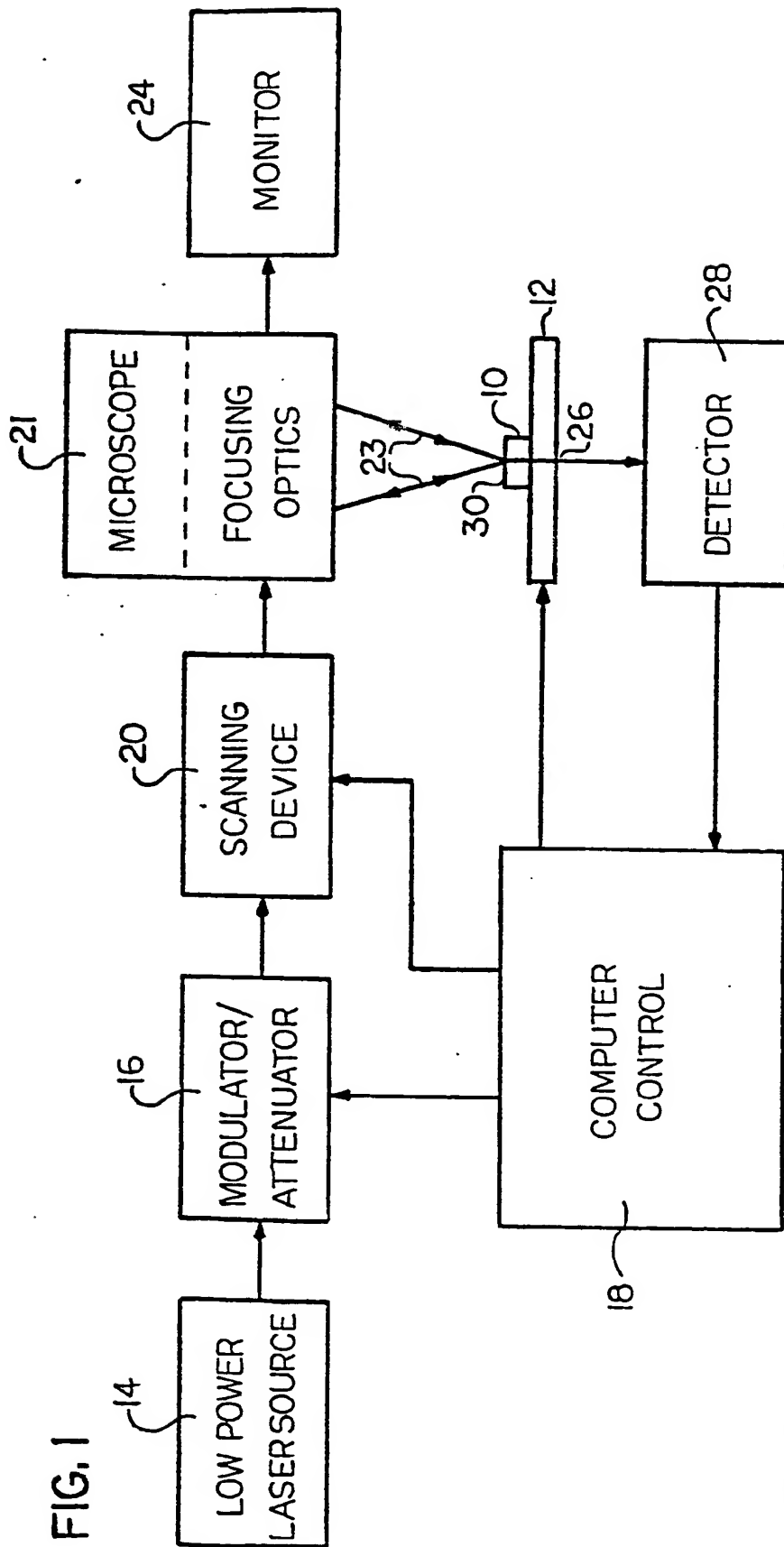
means coupled to said laser source for  
scanning and positioning said beam across a clear  
defect of the photomask;

10 means coupled to said laser source for  
positioning said beam at a clear defect of the  
photomask;

means coupled to said scanning and  
positioning means for focusing said beam on the clear  
15 defect surface of the photomask for localized heating  
of an area of the substrate to which said laser beam is  
incident to thermally decompose molecules of said  
compound on the heated area to deposit a metal film  
thereon;

20 means for venting said cell to remove said  
gaseous compound from said cell;

means for scanning and positioning said laser  
beam across an opaque defect of the photomask to vaporize  
the metalization causing the opaque defect.



(18)



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(54) Laser-based system for the total repair of photomasks.

(57) A low power laser-based system for repairing clear and opaque defects in a photomask. The system includes a laser source for providing a beam having a wavelength between 0.40  $\mu\text{m}$  and 2.0  $\mu\text{m}$ . The beam is coupled to a computer controlled scanning device which scans the beam across a defective area of the photomask to repair the defect by thermal deposition of micron-size films on the defect or by laser-induced degradation of a polymer coating the defect. Excess metal is removed from the photomask surface via laser vaporization.



European Patent  
Office

# EUROPEAN SEARCH REPORT

0165685

Application Number

EP 85 30 3091

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl. 4)
X,Y	ELECTRON DEVICE LETTERS, vol. EDL-1, no. 6, June 1980, pages 101-103, IEEE, New York, US; D.J. EHRLICH et al.: "One-step repair of transparent defects in hard-surface photolithographic masks via laser photodeposition" * Whole document *	1-51	G 03 F 1/00
X,Y	PATENT ABSTRACTS OF JAPAN, vol. 6, no. 46 (P-107)[924], 24th March 1982; & JP-A-56 162 748 (HITACHI SEISAKUSHO K.K.) 14-12-1981	1-51	
Y	US-A-4 042 006 (A. ENGL) * Column 6, lines 28-43 *	1-51	
X	US-A-4 190 759 (M. HONGO et al.) * Figures; claims *	1-51	
X	US-A-4 444 801 (M. HONGO et al.) * Figures *	1-51	
A	PATENT ABSTRACTS OF JAPAN, vol. 5, no. 23 (E-45)[695], 12th February 1981; & JP-A-55 150 226 (HITACHI SEISAKUSHO K.K.) 22-11-1980	1-51	TECHNICAL FIELDS SEARCHED (Int. Cl. 4)
A	US-A-4 340 654 (J.G. CAMPI) * Figures *	1-51	G 03 F 1/00
A	EP-A-0 069 361 (M. HONGO et al.) * Claims *	1-51	
A	US-A-3 364 087 (R. SOLOMON) * Claims *	1-51	
The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 09-11-1987	Examiner RASSCHAERT A.
<b>CATEGORY OF CITED DOCUMENTS</b>			
X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document		T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application I : document cited for other reasons & : member of the same patent family, corresponding document	